

[illegible]

~~Carbon-30: UHV-CVD Si:C @500C using 2% C₂H₄/He~~

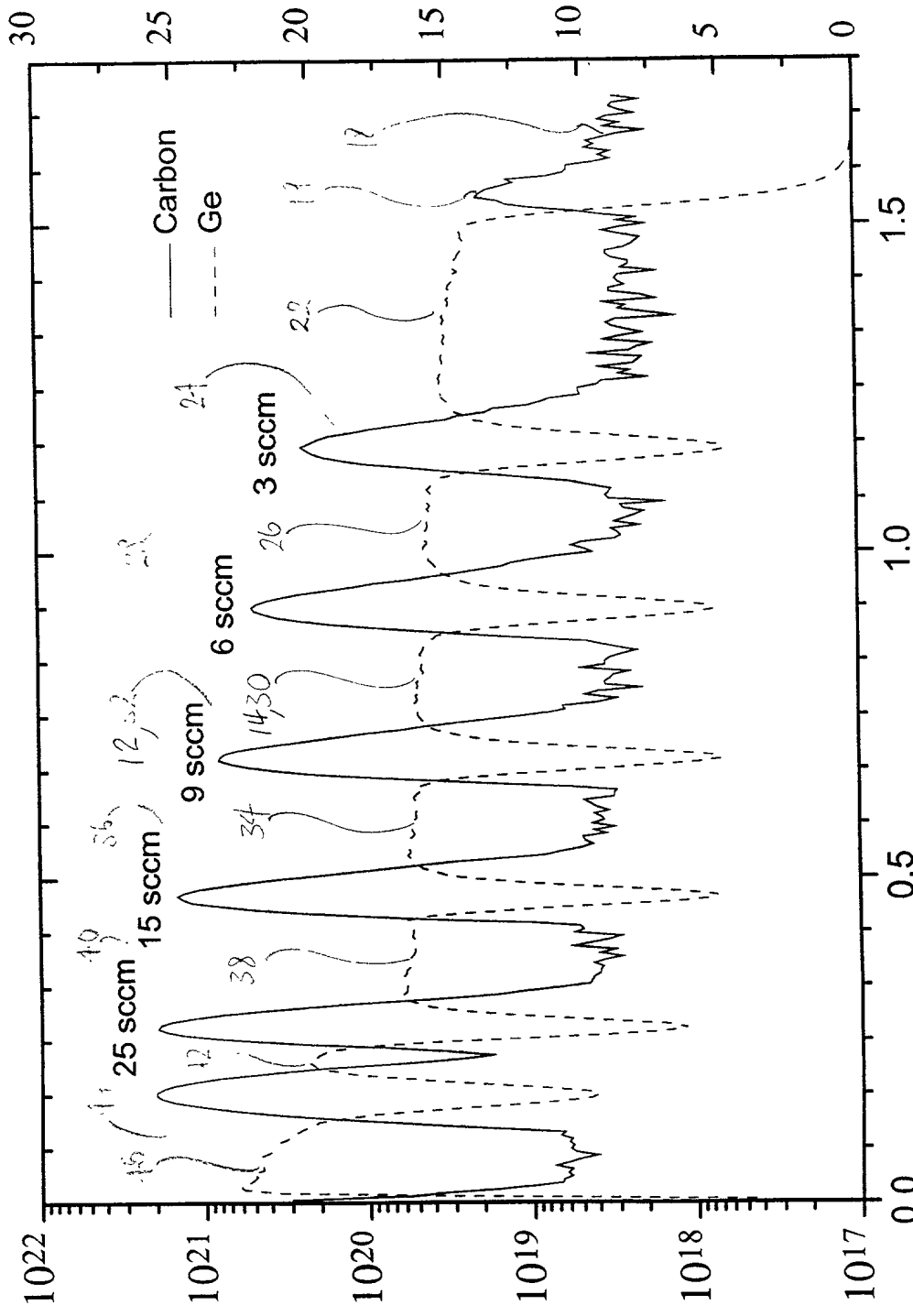


Figure 1

Carbon-30: UHV-CVD SiB:C @500C w/ 2% C₂H₄/He

"Poly-crystalline
Growth"

2.00 x 10²¹ cm⁻³ (@ 35 cc)

1.94 x 10²¹ cm⁻³ (@ 25 cc)

1.46 x 10²¹ cm⁻³ (@ 15 cc)

8.07 x 10²⁰ cm⁻³ (@ 9 cc)

4.97 x 10²⁰ cm⁻³ (@ 6 cc)

2.42 x 10²⁰ cm⁻³ (@ 3 cc)

46'
44'
42'
40'

38'

36'

34'

32'

30'

28'

26'

24'

20

10

Figure 1

2/11

3/11

~~Carbon-32: UHV-CVD-SiGeB:C @500C using 2% C₂H₄/He~~

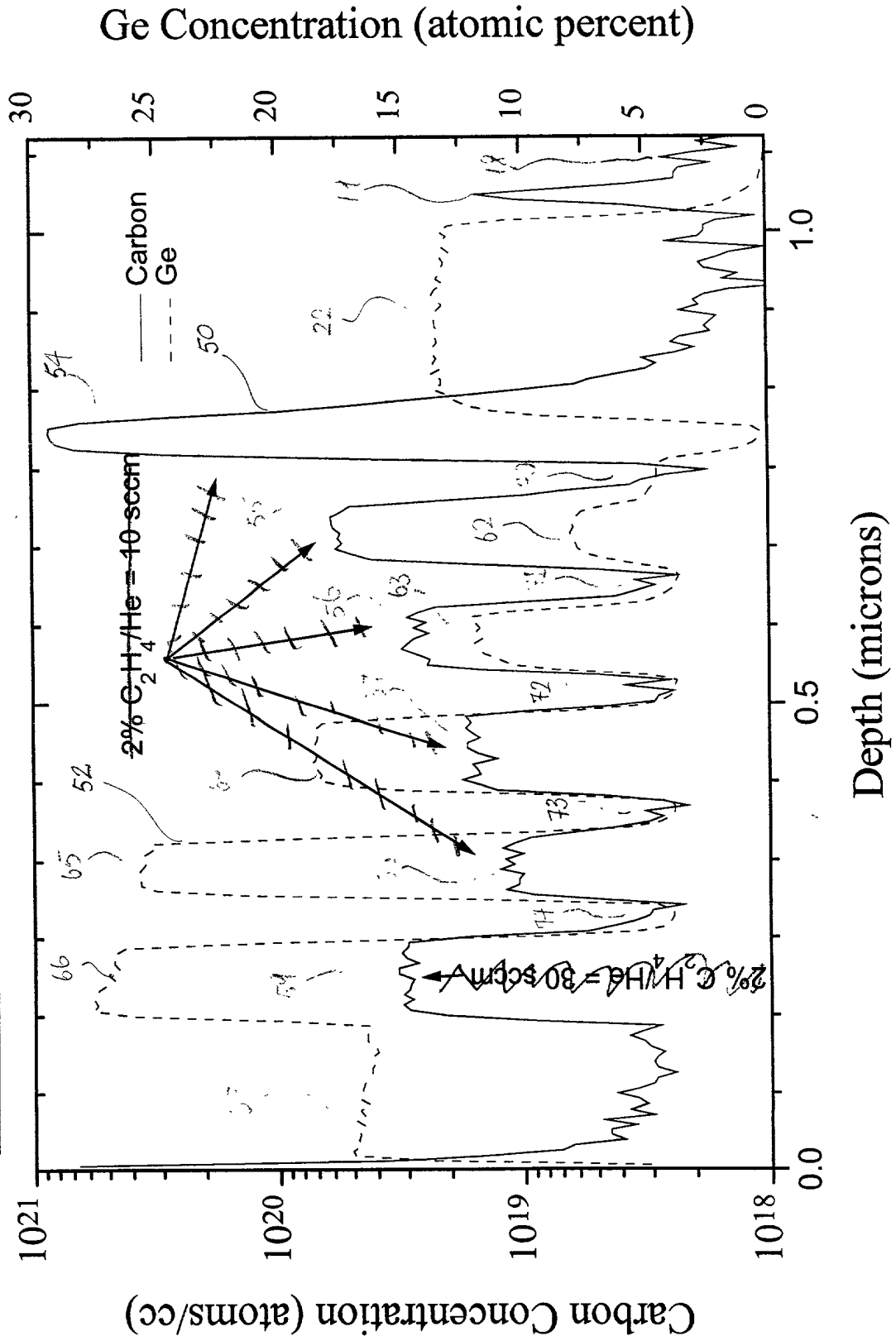


Figure 3

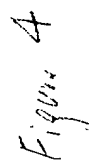
[illegible]~~Carbon-33: UHV-CVD SiGeB:C @500C using 1% C₂H₄/He~~

Figure 4

5/11

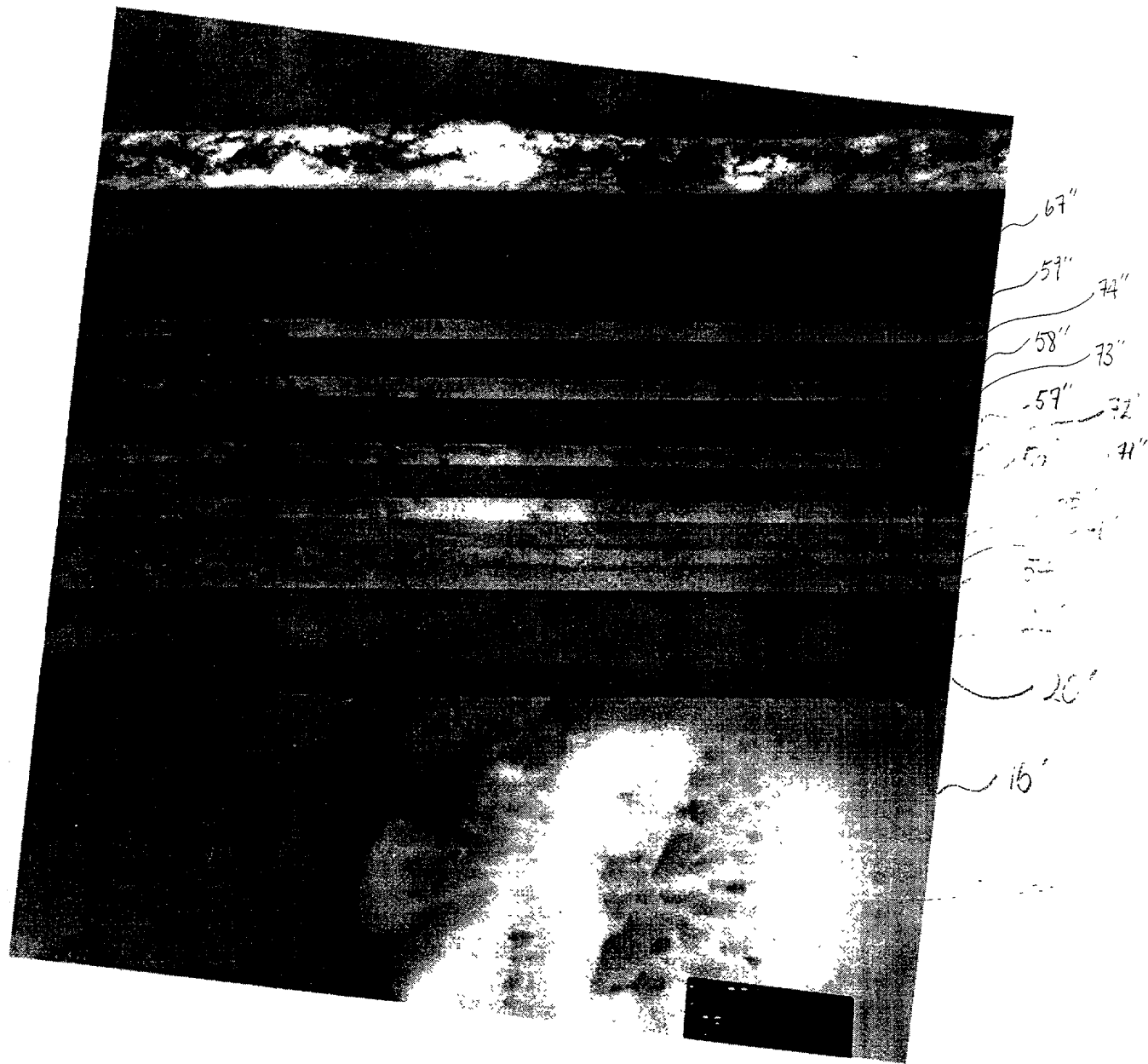
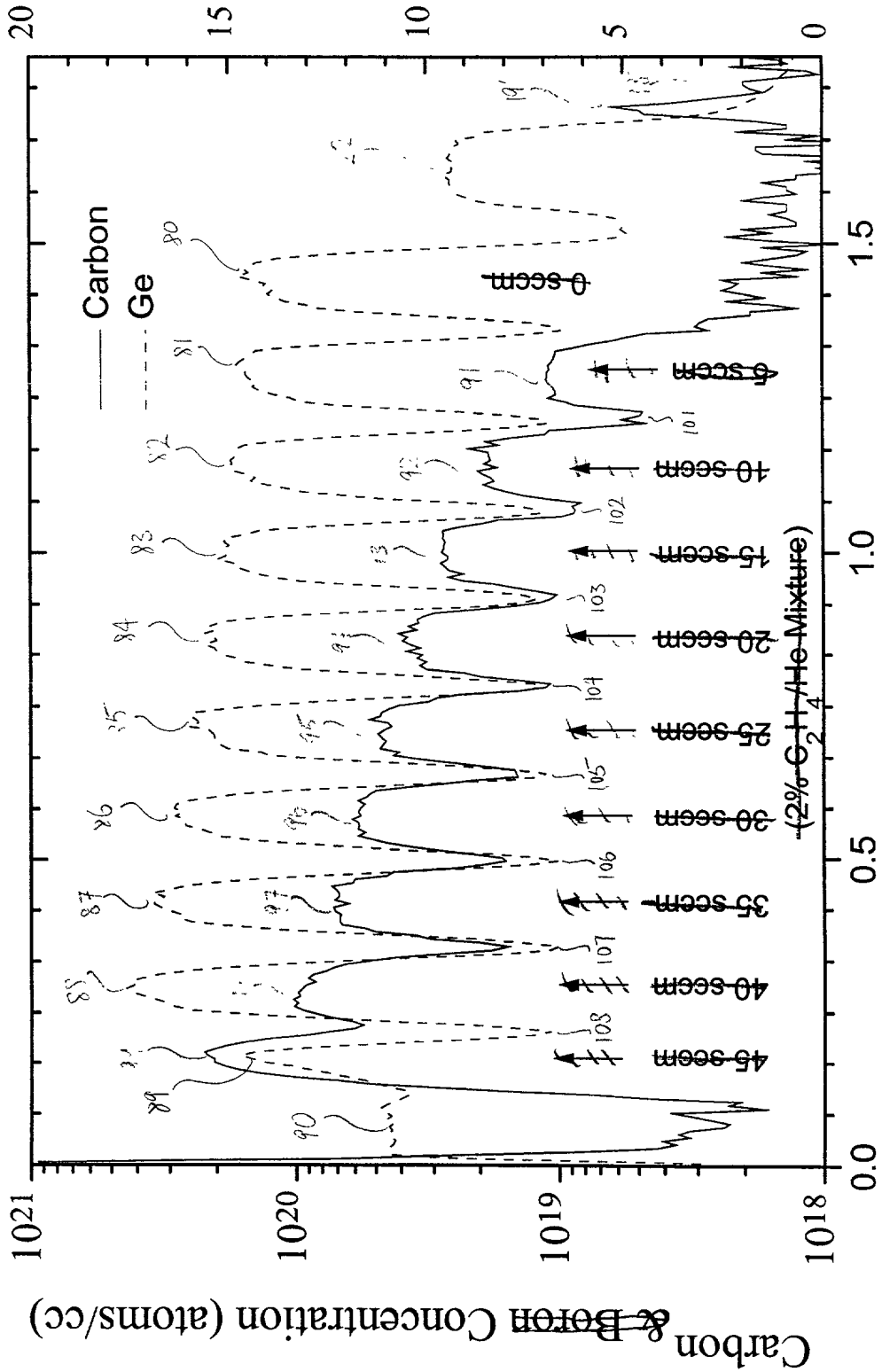


Figure 5

6/11

Ge Concentration (atoms percent)

Carbon 40: UHV-CVD SiGeB:C @500C using 2% C₂H₄/He

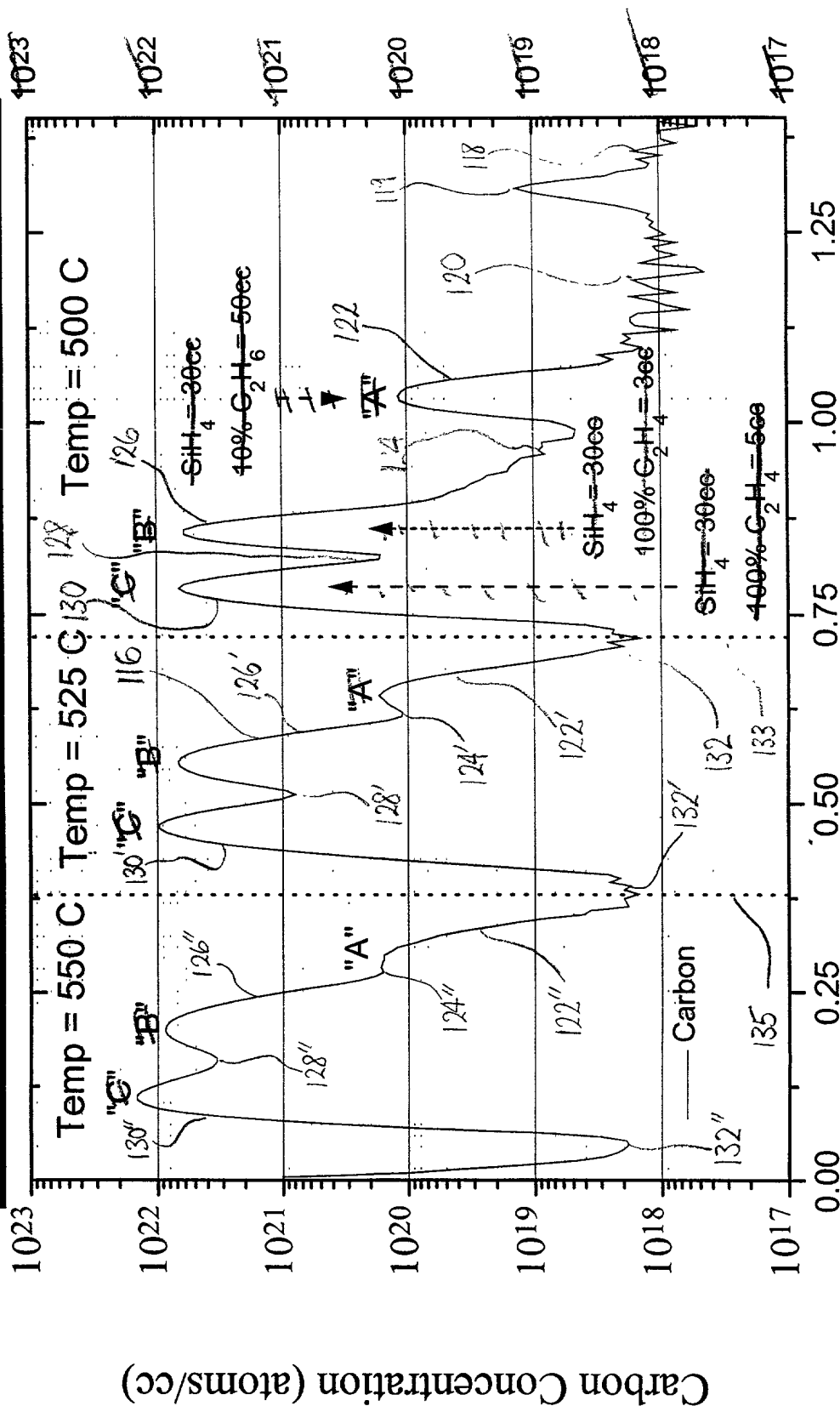


Depth (microns)

Figure 6

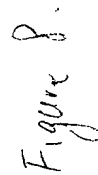
7/11

~~UHV-CVD-SiC with 10% C₂H₆ (99%) & 100% C₂H₄ (99.5%)~~



Depth (microns)

Figure 7

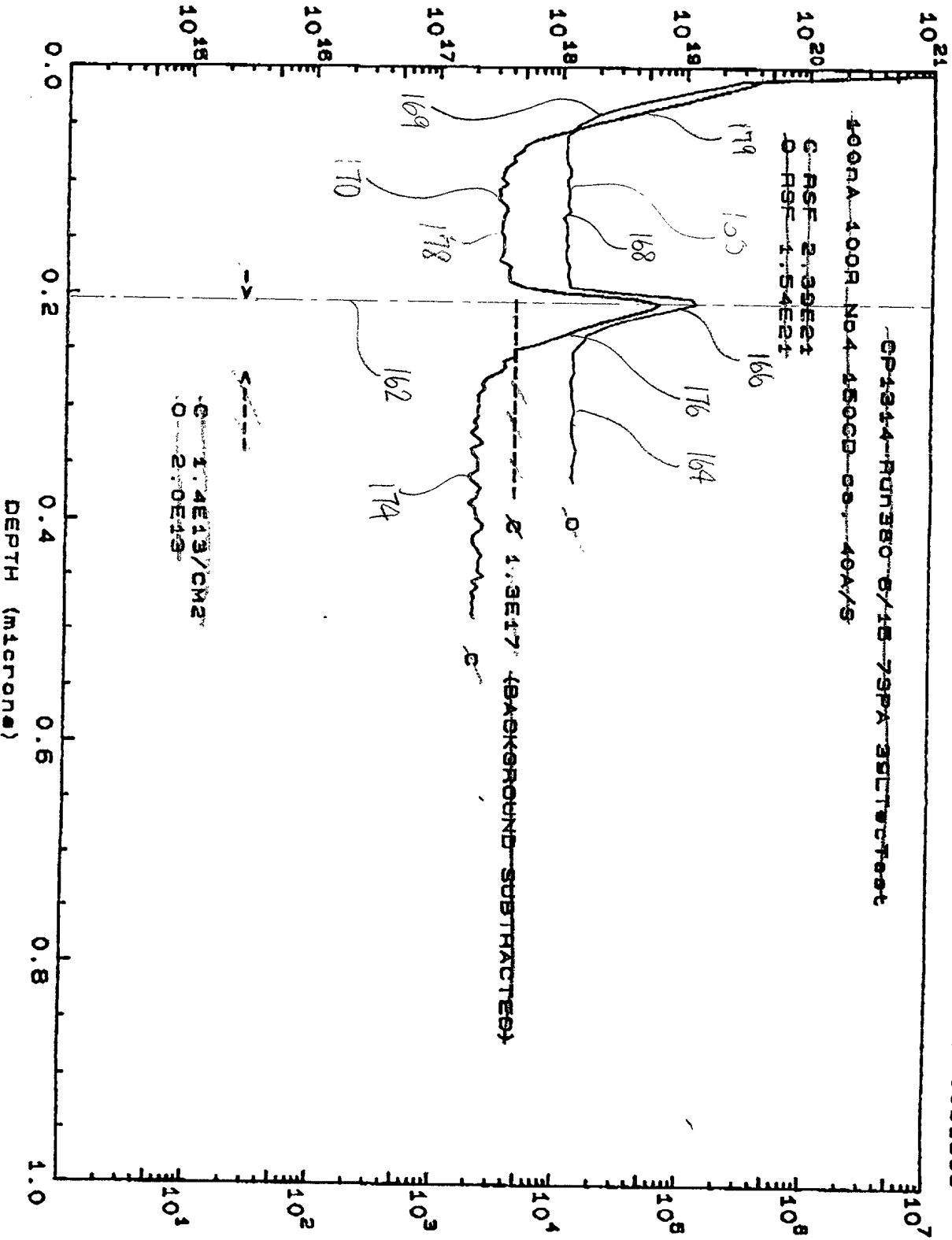


9/11

CONCENTRATION (atoms/cc)

PROCESSED DATA
23 JUN 80 08

IBM Commae 54 (V40/20)
FILE: 0081866



SECONDARY ION COUNTS

FILE: 0081866

Carbon-13: UHV-CVD SiGeB:C at 550°C (C_2H_4) "As-Grown"

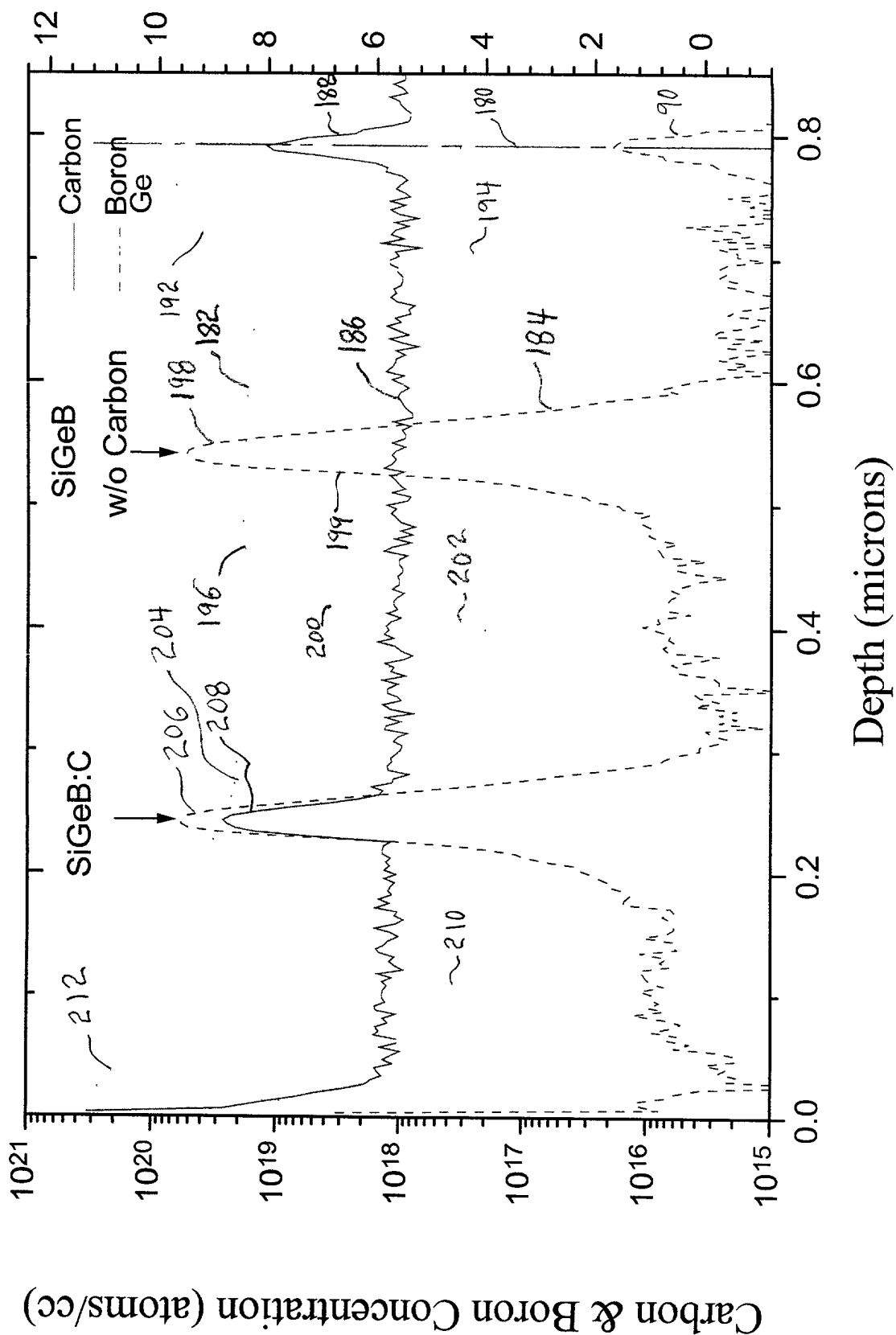


Figure 10

11/11

Impact of Carbon on SiGeB Layers after "850C Furnace Anneal"

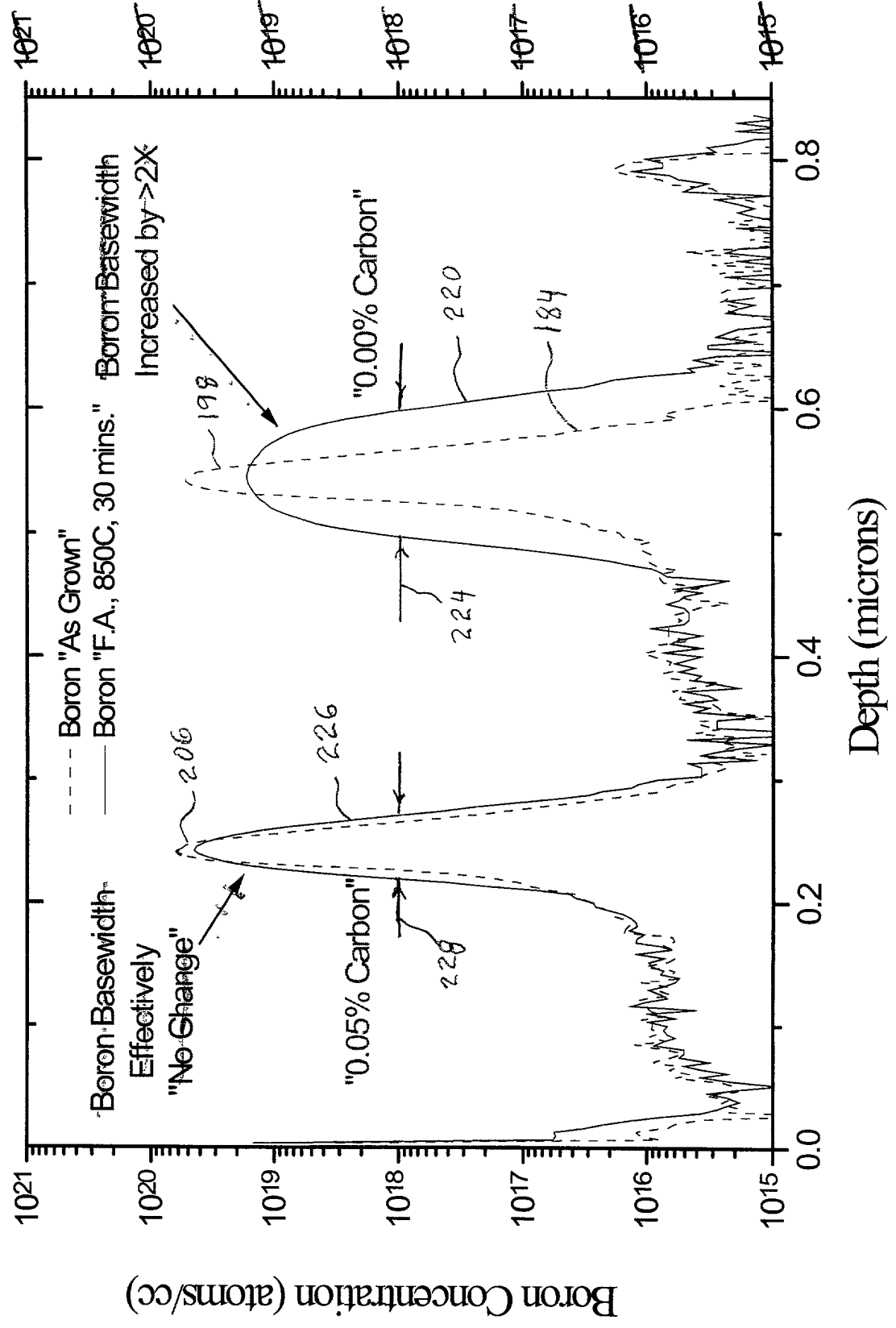


Figure 11